Attorney Docket: 013921-000025



E UNISSED STATES PATENT AND TRADEMARK OFFICE

re application of: Linthicum, Kevin J.

Serial Number: 10/633,952

Filed: August 4, 2003

Group Art Unit: 2815

Examiner: Jerome Jackson, Jr.

For: PENDEOEPITAXIAL METHODS OF FABRICATING GALLIUM NITRIDE SEMICONDUCTOR LAYERS ON SILICON WAFERS OR WAFERS CONTAINING SILICON, AND GALLIUM NITRIDE SEMICONDUCTOR STRUCTURES FABRICATED THEREBY

Commissioner for Patents PO Box 1450 Alexandria, VA 22313-1450

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.56 AND 37 C.F.R. § 1.97

It is respectfully requested that the document listed on the attached Form PTO/SB/08A be considered by the Patent and Trademark Office in the above-referenced application and made of record therein. A full text copy of the relevant non-U.S. patent documents are enclosed. This information disclosure statement submitted herewith is being filed within three months of the filing date of the application or date of entry into the national stage of an international application or before the mailing date of a first Office action on the merits, whichever event occurs last.

Respectfully submitted,

By:

Steven B. Phillips
Registration No. 37,911
Attorney for Applicant
Moore & Van Allen, PLLC
2200 West Main Street, Suite 800

Durham, NC 27705 Phone: 919-286-8000

Facsimile: 919-286-8199

October 7, 2004

Date

## **CERTIFICATE OF EXPRESS MAILING**

I hereby certify that this correspondence is being deposited with the US Postal Service Express Mail (EV 501573525) on October 7, 2004, in an envelope addressed to Commissioner of Patents, PO Box 1450, Alexandria, VA 22313-1450

m KROU

PTO/SB/08a (08-03)

Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE
to a collection of information unless it contains a valid OMB control number.

Unae	er ne Paperwork Reduction	Act of 1995, no persons	s are required to respond to a collection of it	normation unless it contains a valid Olvib cont	ioi numbei.				
a postituje	e for form 1449A/PTO	TRADEMARK	·	Complete if Known					
		•	Application Number	10/633,952					
· I	INFQRMATION D	DISCLOSURE	Filing Date	August 4, 2003					
	STATEMENT BY	APPLICANT	First Named Inventor	Linthicum, Kevin J.					
PADE	MATE		Art Unit	2815					
	(use as many sheets		Examiner Name	Jerome Jackson, Jr.					
Sheet	1	of	Attorney Docket Number	013921-000025					

		· ·	U.S. PATENT	DOCUMENTS	
Examiner Initials'	Cite No. <sup>1</sup>	Document Number  Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	5,633,192	05-27-97	Moustakas et al.	
	AB	5,686,738	11-11-97	Moustakas	
	AC	5,760,426	06-02-98	Marx et al.	
	AD	5,838,029	11-17-98	Shakuda	
	AE	6,146,457	11-14-00	Solomon	

Foreign Patent Document    Cite   No.1			-,,						
Foreign Patent Document   Publication Date   Name of Patentee or Applicant of Cited Document   Publication Date   Name of Patentee or Applicant of Cited Document   Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear				FOREIGN	PATENT DO	UMENTS			
Cite No.1 Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.  AF Lahreche et al., "Growth of High Quality GaN by low pressure metal-organic vapour phase epitaxy (LP_MOVPE) from 3D islands and lateral overgrowth," Journal of Crystal Growth, 205 (1999) 245-252  Lei et al., "Epitaxial growth of zinc blende and wurtzitic gallium nitride thin films on (001) silicon," Applied Physics Letters, 59(8), 19 August 1991				ment	Publication Date	Name of Patentee		Where Relevant Passages	1 1
Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.  Lahreche et al., "Growth of High Quality GaN by low pressure metal-organic vapour phase epitaxy (LP_MOVPE) from 3D islands and lateral overgrowth," Journal of Crystal Growth, 205 (1999) 245-252  Lei et al., "Epitaxial growth of zinc blende and wurtzitic gallium nitride thin films on (001) silicon," Applied Physics Letters, 59(8), 19 August 1991				NON PATENT	LITERATURE	OCUMENTS			
AF (LP_MOVPE) from 3D islands and lateral overgrowth," <u>Journal of Crystal Growth</u> , 205 (1999) 245-252  Lei et al., "Epitaxial growth of zinc blende and wurtzitic gallium nitride thin films on (001) silicon," <u>Applied Physics Letters</u> , 59(8), 19 August 1991	iner		magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or					T²	
AG Applied Physics Letters, 59(8), 19 August 1991		AF							
		AG							
					<i>5</i> 4				
							-		
Examiner Date	Evamin	er				Date	<u> </u>		

Signature		Considered		
*EXAMINER: Initial if ref	erence considered, whether or not citation is in conformance with MPEP 609.	Draw line through ci	tation if not in conformance and not consid	erec

Include copy of this form with next communication to applicant. <sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.